

N-channel 30 V 9.8 mΩ logic level MOSFET in LFPAK using NextPower technology

Rev. 2 — 1 September 2011

Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, and QOSS for high system efficiencies at low and high loads

Synchronous buck regulator

1.3 Applications

- DC-to-DC converters
- Load switching

1.4 Quick reference data

Table 1. Quick reference data

	guick reference data					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	30	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; see <u>Figure 1</u>	-	-	44	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	34	W
Tj	junction temperature		-55	-	175	°C
Static cha	aracteristics					
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 15 A; T _j = 25 °C; see <u>Figure 12</u>	-	10.3	12.1	mΩ
		$V_{GS} = 10 \text{ V}; \text{ I}_{D} = 15 \text{ A};$	-	8.3	9.8	mΩ

 $T_i = 25 \text{ °C}; \text{ see } Figure 12$



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Table 1.	Quick reference data .	continued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic	characteristics					
Q_{GD}	gate-drain charge	V_{GS} = 4.5 V; I_D = 15 A; V_{DS} = 15 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	1.6	-	nC
Q _{G(tot)}	total gate charge	V_{GS} = 4.5 V; I_D = 15 A; V_{DS} = 15 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	5	-	nC

2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		2
2	S	source	mb ()	
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain	មិតិចំពុំ	mbb076 S
			1 2 3 4 SOT669 (LFPAK; Power-SO8)	

3. Ordering information

Table 3. Orderin	g information		
Type number	Package		
	Name	Description	Version
PSMN9R5-30YLC	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669

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Limiting values 4.

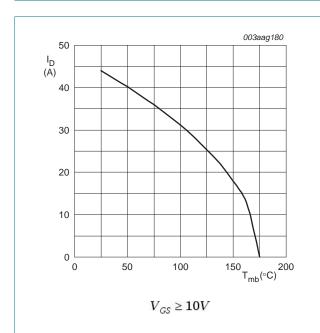
Limiting values Table 4.

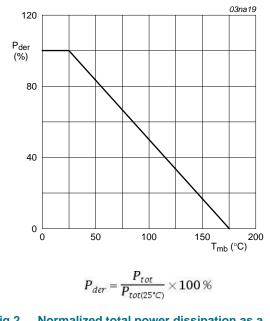
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	30	V
V _{DGR}	drain-gate voltage	25 °C \leq T _j \leq 175 °C; R _{GS} = 20 k Ω	-	30	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u>	-	44	А
		V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	-	31	А
I _{DM}	peak drain current	pulsed; t _p ≤ 10 µs; T _{mb} = 25 °C; see <u>Figure 4</u>	-	177	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	34	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
V _{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	150	-	V
Source-drai	n diode				
ls	source current	T _{mb} = 25 °C	-	31	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	177	А
Avalanche r	uggedness				
E _{DS(AL)S}	non-repetitive drain-source	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 44 A;	-	9	mJ

avalanche energy

see Figure 3



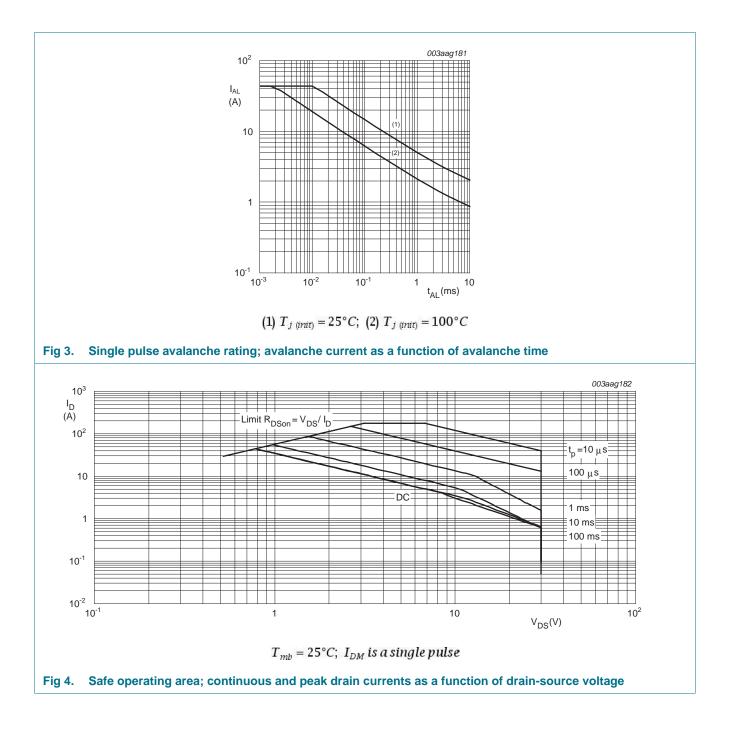






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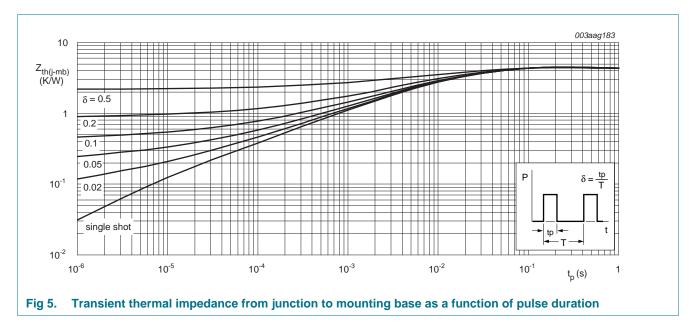


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5. Thermal characteristics

Table 5. T	hermal	characteristics
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Rev. 2 — 1 September 2011

N-channel 30 V 9.8 mΩ logic level MOSFET in LFPAK using NextPower technology

Characteristics 6.

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ C$	30	-	-	V
	voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ C$	27	-	-	V
V _{GS(th)} gate	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	1.05	1.66	1.95	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C}$	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	2.25	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μΑ
I _{GSS}	gate leakage current	V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 15 A; T _j = 25 °C; see <u>Figure 12</u>	-	10.3	12.1	mΩ
		V_{GS} = 4.5 V; I_D = 15 A; T_j = 150 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	20.3	mΩ
	V_{GS} = 10 V; I_D = 15 A; T_j = 25 °C; see <u>Figure 12</u>	-	8.3	9.8	mΩ	
		V_{GS} = 10 V; I_D = 15 A; T_j = 150 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	16.5	mΩ
R _G	gate resistance	f = 1 MHz	-	2.35	4.7	Ω
Dynamic	characteristics					
Q _{G(tot)} total gate charge	total gate charge	$I_D = 15 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V}; \text{see}$ Figure 14; see Figure 15	-	10.4	-	nC
		$I_D = 15 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ see Figure 14; see Figure 15	-	5	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	10.1	-	nC
Q _{GS}	gate-source charge	$I_D = 15 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	1.6	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see Figure 14; see Figure 15	-	1.1	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	0.5	-	nC
Q _{GD}	gate-drain charge		-	1.6	-	nC
V _{GS(pl)}	gate-source plateau voltage	$I_D = 15 \text{ A}; V_{DS} = 15 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 15}$	-	2.77	-	V
C _{iss}	input capacitance	$V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; \text{ f} = 1 \text{ MHz};$	-	681	-	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{1000}$	-	169	-	pF
C _{rss}	reverse transfer capacitance		-	50	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; R _L = 1 Ω; V _{GS} = 4.5 V;	-	13	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \ \Omega$	-	8.8	-	ns
t _{d(off)}	turn-off delay time		-	15	-	ns
t _f	fall time		-	4.7	-	ns

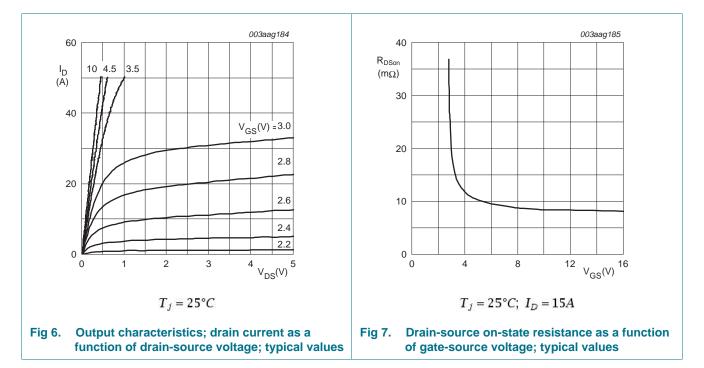
PSMN9R5-30YLC **Product data sheet**

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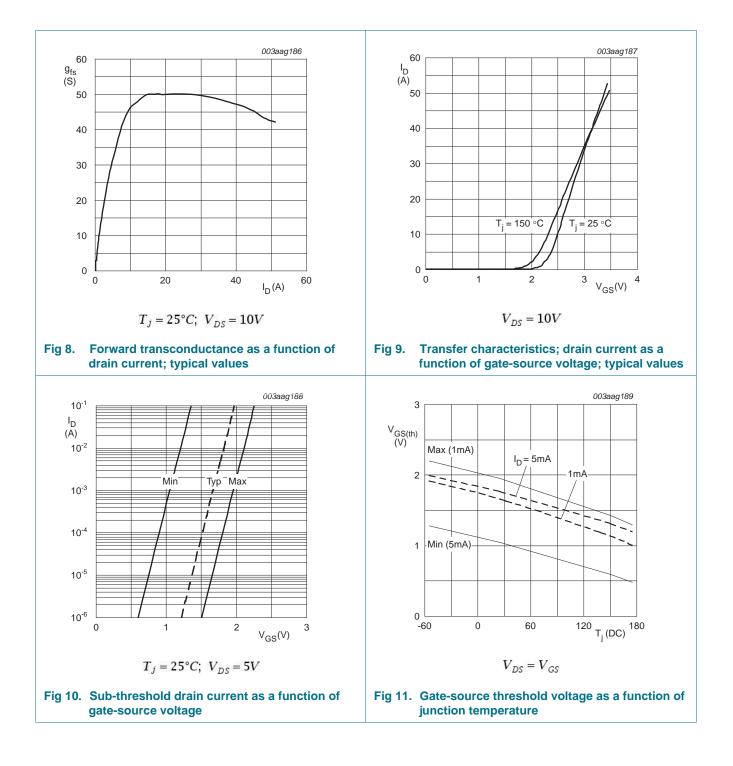
Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q _{oss}	output charge	V_{GS} = 0 V; V_{DS} = 15 V; f = 1 MHz; T _j = 25 °C	-	4.4	-	nC
Source-dra	in diode					
V _{SD}	source-drain voltage	I _S = 15 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 17</u>	-	0.86	1.1	V
t _{rr}	reverse recovery time	I _S = 15 A; dI _S /dt = -100 A/µs;	-	10	-	ns
Q _r	recovered charge	$V_{GS} = 0 V; V_{DS} = 15 V$	-	18	-	nC
t _a	reverse recovery rise time	V _{GS} = 0 V; I _S = 15 A;	-	11	-	ns
t _b	reverse recovery fall time	dl _S /dt = -100 A/µs; V _{DS} = 15 V; see <u>Figure 18</u>	-	7	-	ns



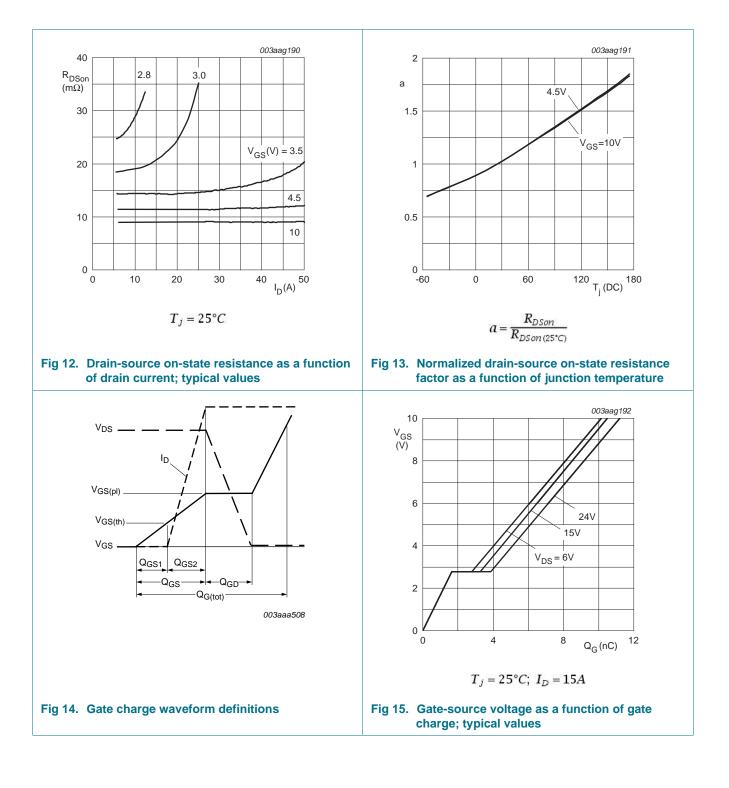
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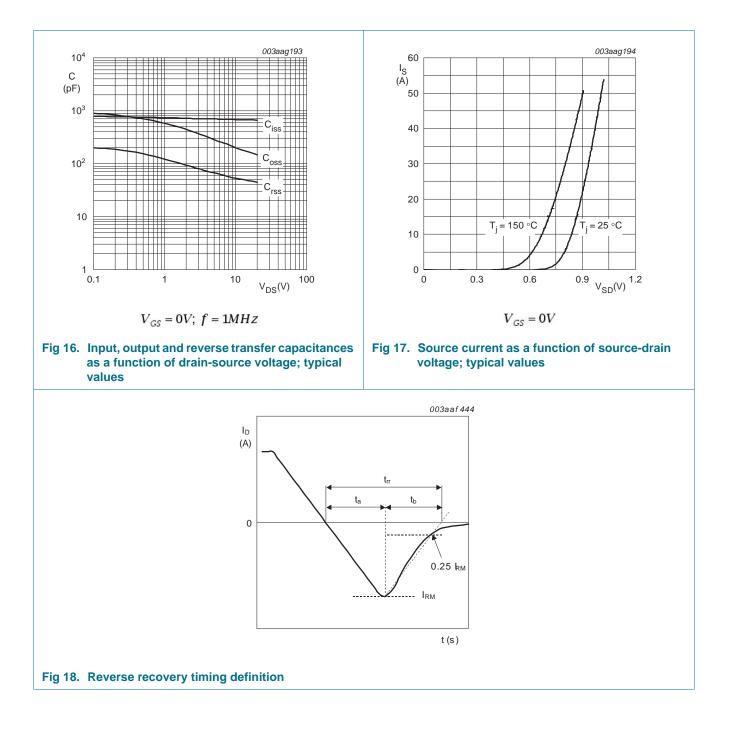
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7. Package outline

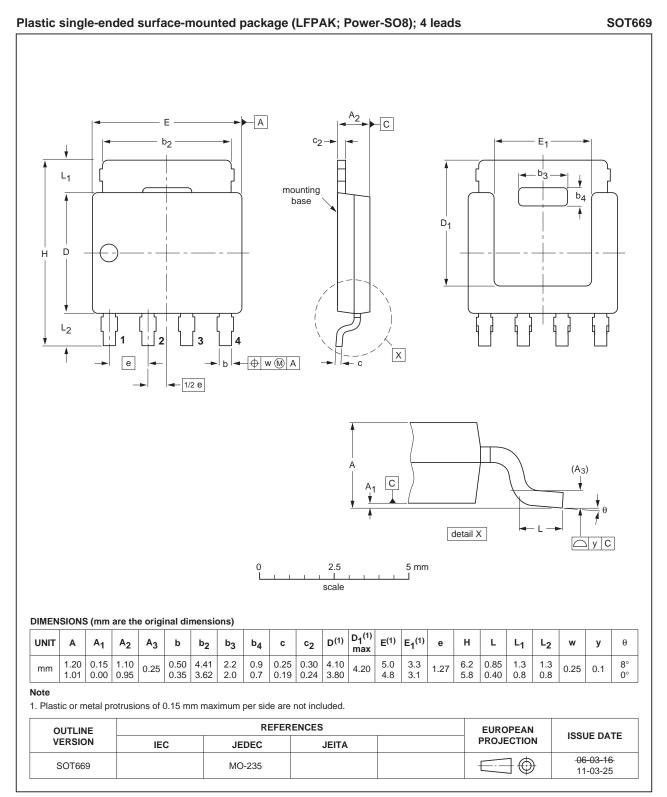


Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

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8. Revision history

Table 7.Revision h	istory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN9R5-30YLC v.2	20110901	Product data sheet	-	PSMN9R5-30YLC v.1
Modifications:	 Status change 	ed from preliminary to produc	t.	
	 Various change 	jes to content.		
PSMN9R5-30YLC v.1	20110711	Preliminary data shee	t -	-

N-channel 30 V 9.8 mΩ logic level MOSFET in LFPAK using NextPower technology

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status 3	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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11. Contents

1	Product profile1
1.1	General description1
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values
5	Thermal characteristics5
6	Characteristics6
7	Package outline11
8	Revision history12
9	Legal information13
9.1	Data sheet status
9.2	Definitions
9.3	Disclaimers
9.4	Trademarks14
10	Contact information14

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